High Voltage PNP Epitaxial Planar Transistor

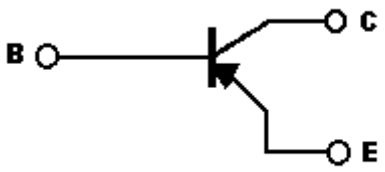
BTP9050N3

Description

- High breakdown voltage. (BV_{CEO}=-500V)
- Low saturation voltage, typical $V_{CE(sat)}$ =-0.2V at Ic/I_B =-20mA/-2mA.
- Complementary to BTNA45N3
- Pb-free lead plating and halogen-free package

Symbol

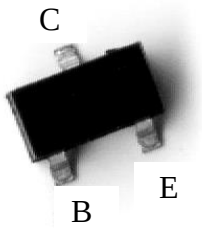
BTP9050N3



B：Base C：Collector
E：Emitter

Outline

SOT-23



Ordering Information

Device	Package	Shipping
BTP9050N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

Packing spec, T1 : 3000 pcs / tape & reel, 7” reel

Product rank, zero for no rank products

Product name

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-500	V
Collector-Emitter Voltage	V_{CEO}	-500	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current(DC)	I_C	-150	mA
Peak Collector Current , single pulse, pulse width tp<1ms	I_{CM}	-500	mA
Peak Base Current, single pulse, pulse width tp<1ms	I_{BM}	-200	mA
Power Dissipation	P_D	300 (Note)	mW
Operating Junction and Storage Temperature Range	Tj ; Tstg	-55~+150	°C

Note : Device mounted on a FR-4 PCB, single sided copper, tin plated and standard footprint.

Thermal Characteristics

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient, in free air (Note)	Rth,j-a	417	°C/W
Thermal Resistance, Junction-to-Solder point	Rth,j-sp	70	

Note : Device mounted on a FR-4 PCB, single sided copper, tin plated and standard footprint.

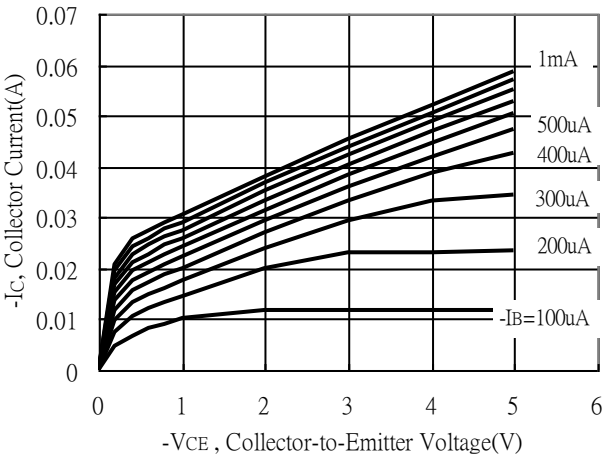
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-500	-	-	V	I_C=-100μA
BV_{CEO}	-500	-	-	V	I_C=-1mA
BV_{EBO}	-5	-	-	V	I_E=-50μA
I_{CBO}	-	-	-100	nA	V_{CB}=-480V
I_{CES}	-	-	-100	nA	V_{CE}=-480V, V_{BE}=0V
I_{EBO}	-	-	-1	μA	V_{EB}=-5V
*$V_{CE(sat)}$	-	-	-0.5	V	I_C=-20mA, I_B=-2mA
*$V_{CE(sat)}$	-	-	-0.5	V	I_C=-50mA, I_B=-10mA
*$V_{BE(sat)}$	-	-	-0.9	V	I_C=-50mA, I_B=-10mA
*h_{FE} 1	100	-	300	-	V_{CE}=-10V, I_C=-10mA
*h_{FE} 2	80	-	300	-	V_{CE}=-10V, I_C=-50mA
*h_{FE} 3	40	-	-	-	V_{CE}=-10V, I_C=-100mA
f_T	-	50	-	MHz	V_{CE}=-10V, I_C=-10mA, f=10MHz
Cob	-	12	-	pF	V_{CB}=-10V, I_E=0A, f=1MHz
Cib	-	85	-	pF	V_{EB}=-0.5V, I_C=0A, f=1MHz

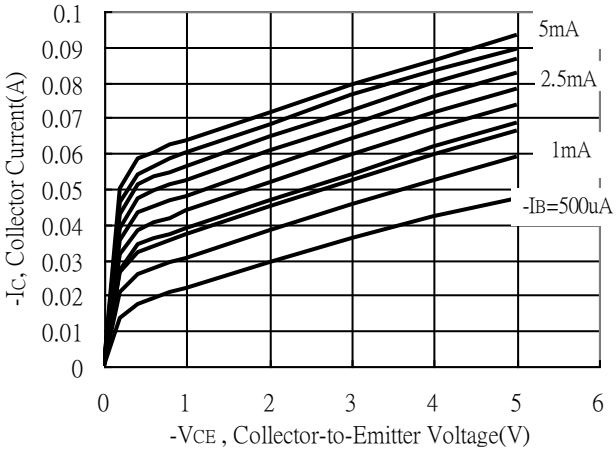
*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Typical Characteristics

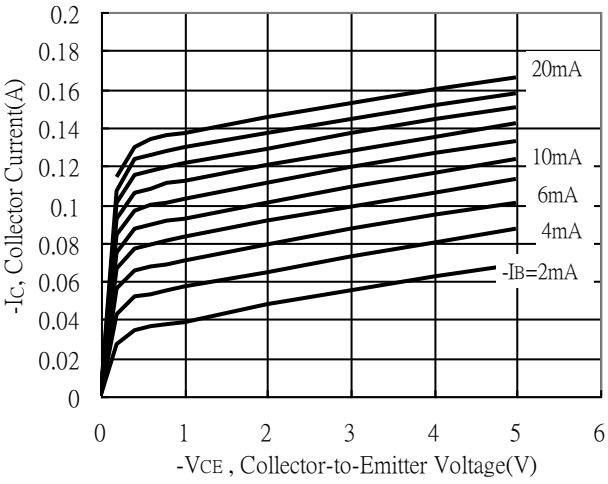
Emitter Grounded Output Characteristics



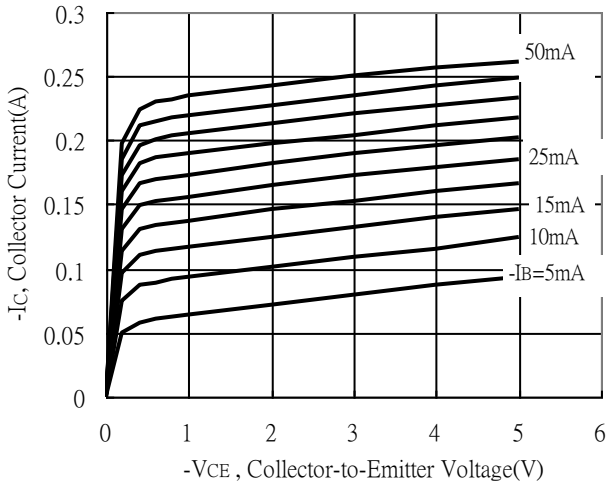
Emitter Grounded Output Characteristics



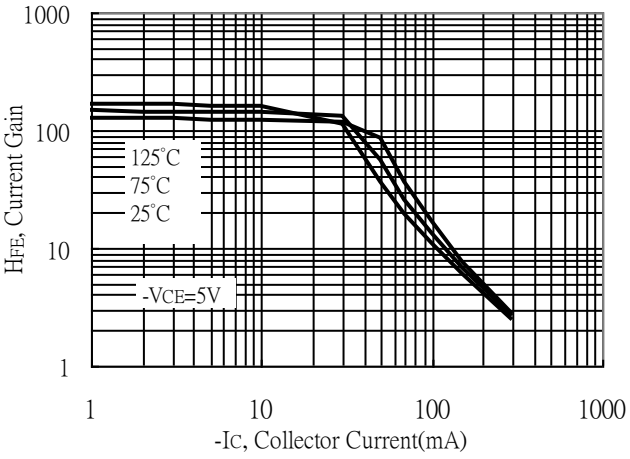
Emitter Grounded Output Characteristics



Emitter Grounded Output Characteristics



Current Gain vs Collector Current



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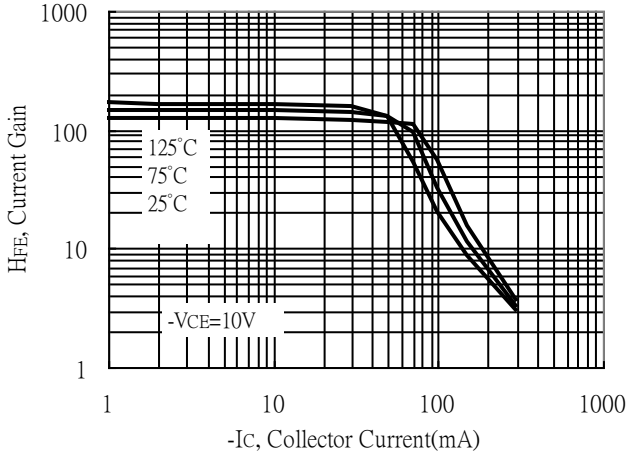
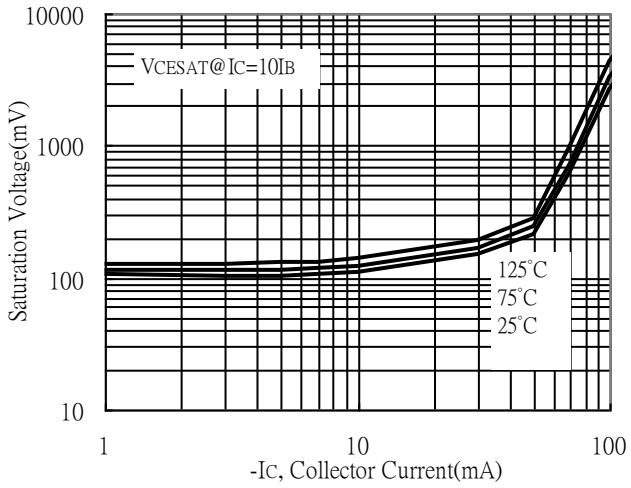
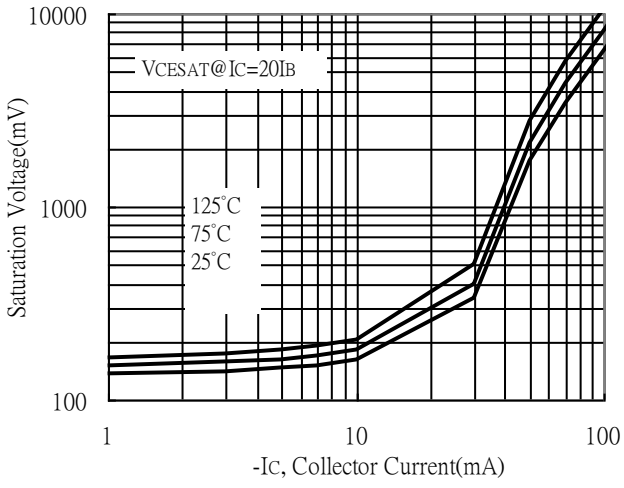


Typical Characteristics

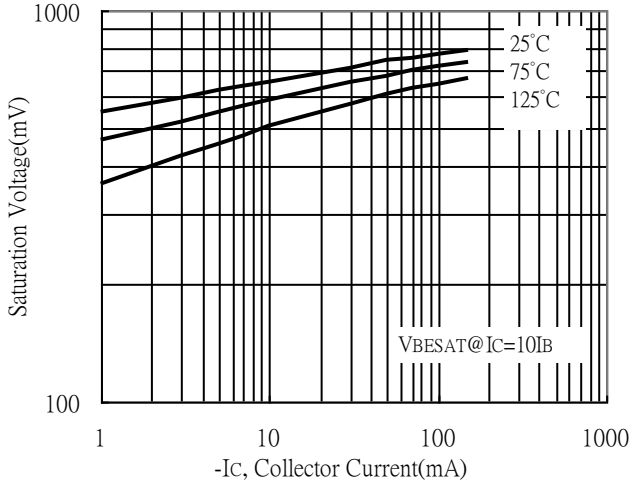
Saturation Voltage vs Collector Current



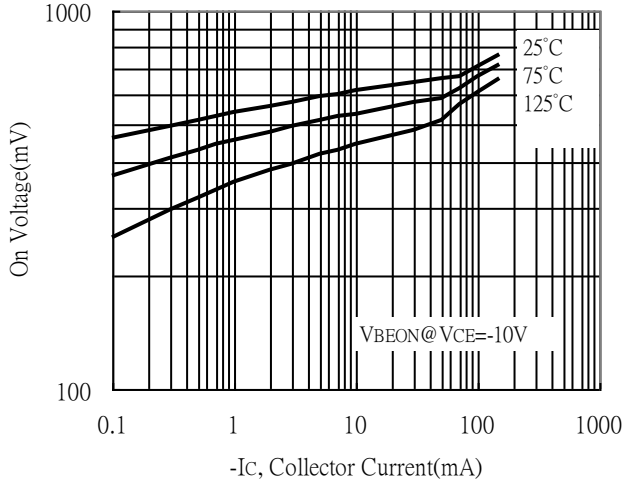
Saturation Voltage vs Collector Current



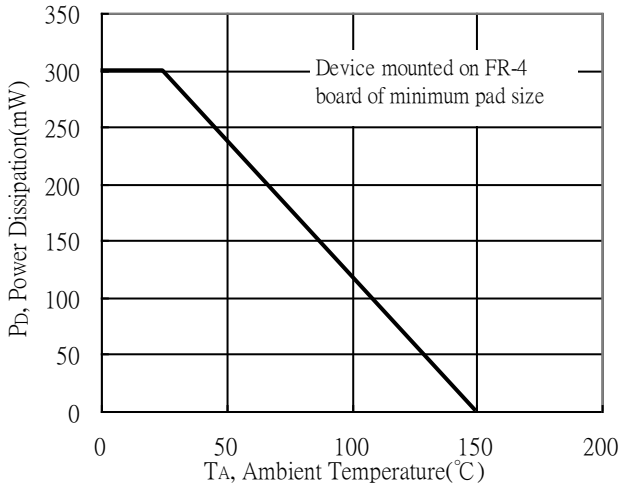
Saturation Voltage vs Collector Current



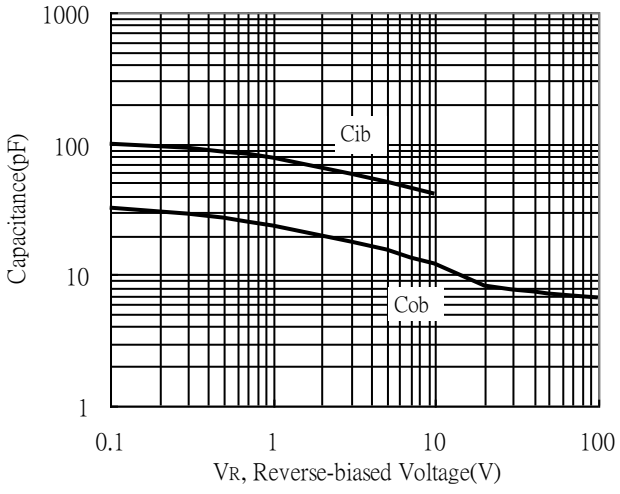
On Voltage vs Collector Current



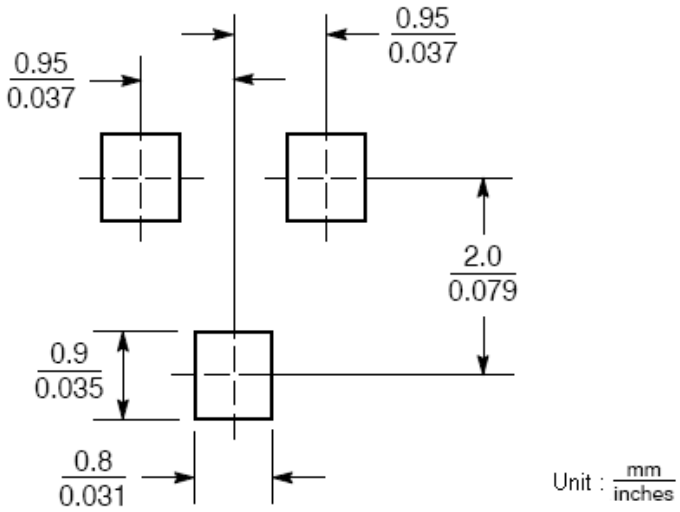
Power Derating Curve



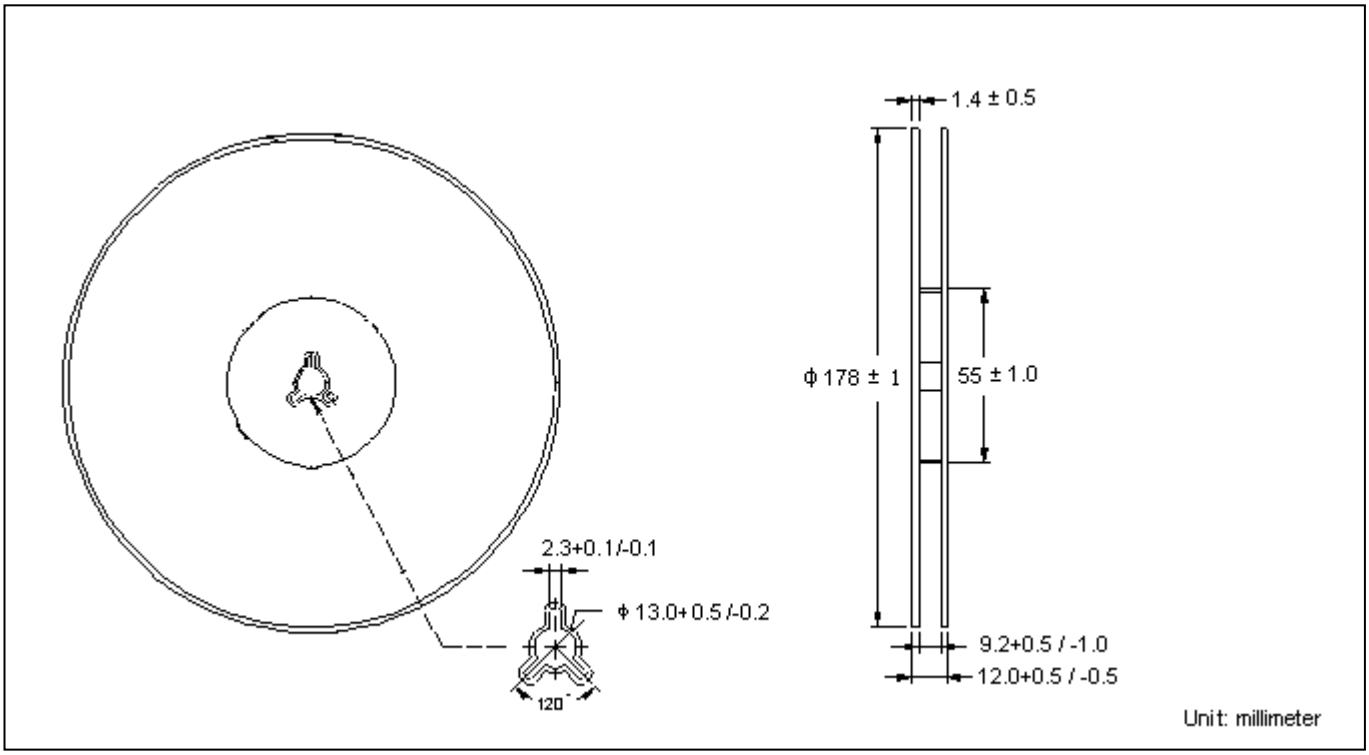
Capacitance vs Reverse-biased Voltage



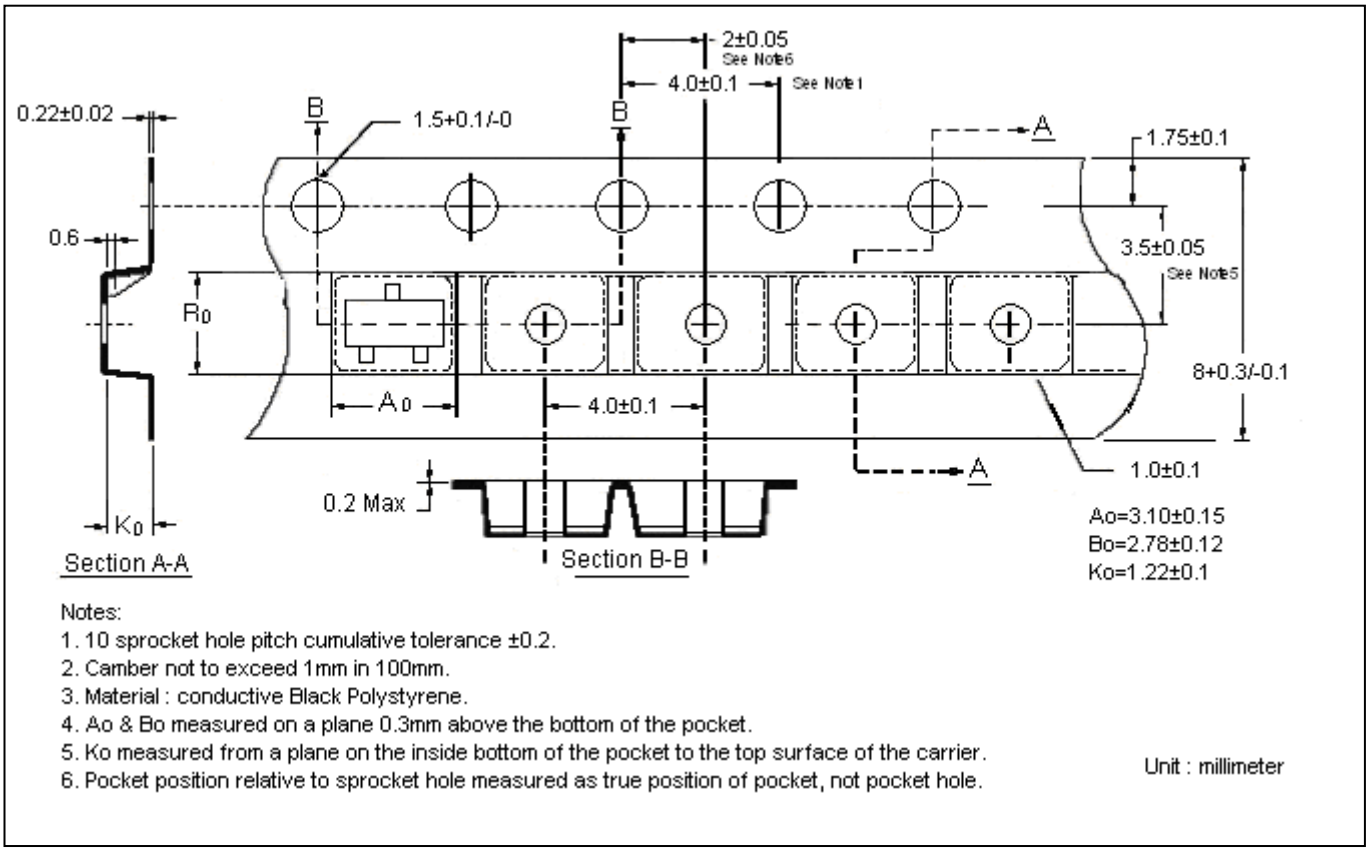
Recommended Soldering Footprint



Reel Dimension



Carrier Tape Dimension



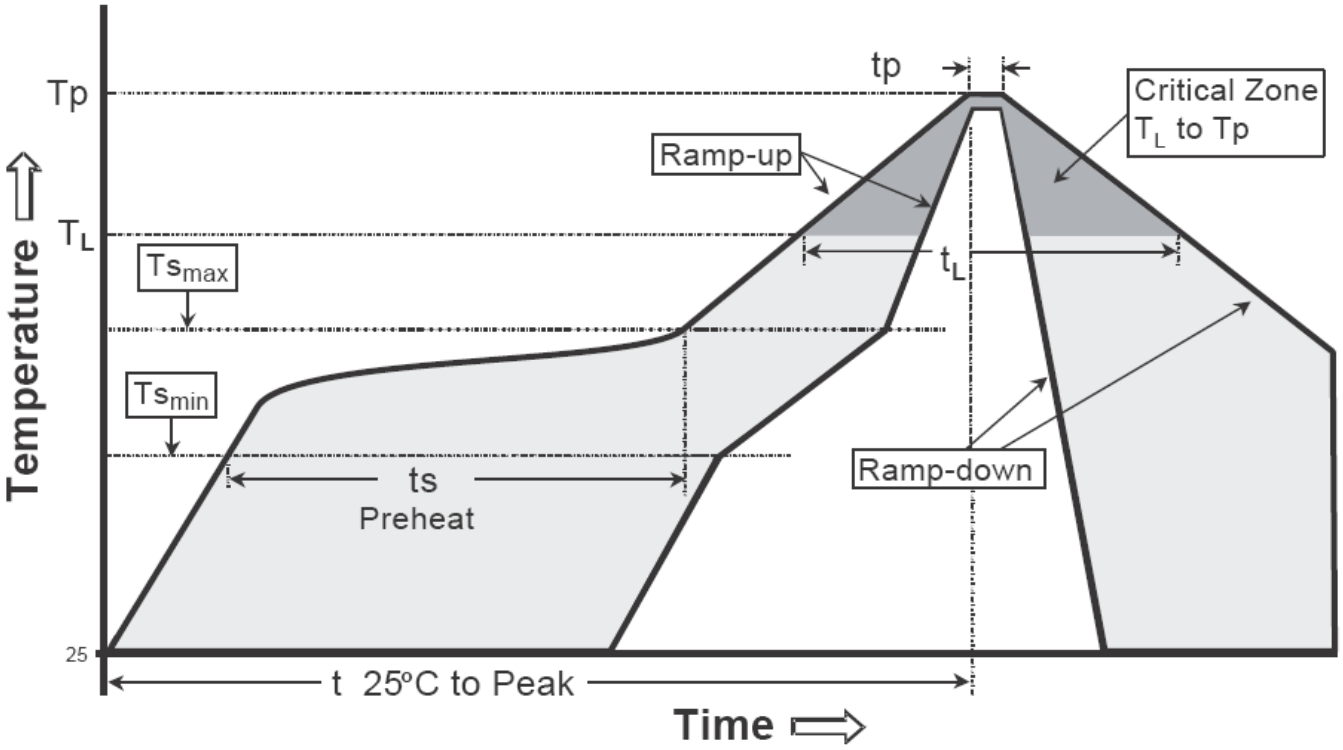
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

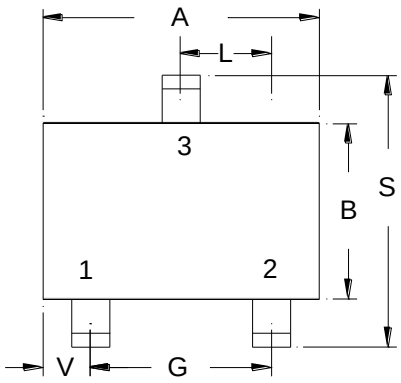
Recommended temperature profile for IR reflow

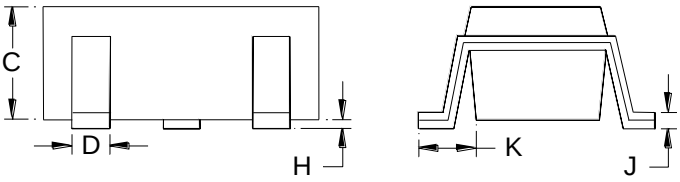


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time(ts min to ts max)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension

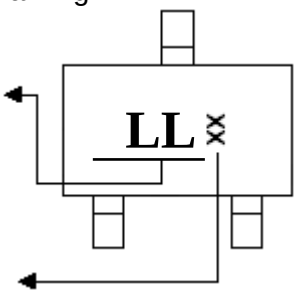




Product Code

Date Code: Year+Month
Year: 7→2007, 8→2008
Month: 1→1, 2→2, • • •
9→9, A→10, B→11, C→12

Marking:



3-Lead SOT-23 Plastic
Surface Mounted Package
CYStek Package Code: N3

Style : Pin 1.Base 2.Emitter 3.Collector

*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0031	0.0071	0.08	0.18
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes : 1.Controlling dimension : millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.